

**SINGLE P-CHANNEL ENHANCEMENT MODE MOSFET**

**Product Summary**

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	$I_D$ max $T_A = +25^\circ C$
-30V	11m $\Omega$ @ $V_{GS} = -10V$	-13A
	17m $\Omega$ @ $V_{GS} = -4.5V$	-9.9A

**Description**

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(on)}$ ) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

**Applications**

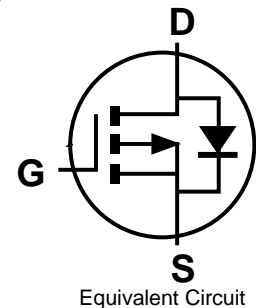
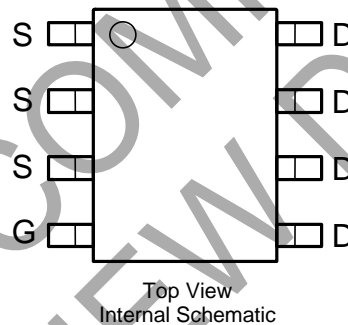
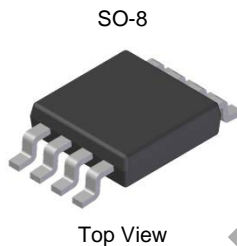
- Backlighting
- Power Management Functions
- DC-DC Converters

**Features and Benefits**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

**Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.074g (Approximate)

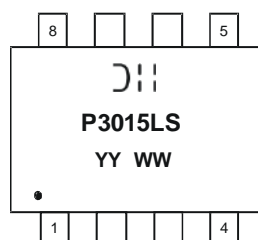
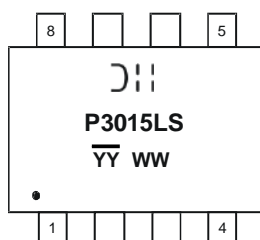


**Ordering Information** (Note 4)

Part Number	Case	Packaging
DMP3015LSS-13	SO-8	2500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

**Marking Information**



- ⌋⌋ = Manufacturer's Marking
- P3015LS = Product Type Marking Code
- YYWW = Date Code Marking
- YY or  $\overline{YY}$  = Year (ex: 13 = 2013)
- WW = Week (01 - 53)
- YY = Date Code Marking for SAT (Shanghai Assembly/ Test site)
- YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	-30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	-13	A
		T <sub>A</sub> = +70°C		-9.75	
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-45	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	2.5	W
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	50	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes: 5. Device mounted on 2 oz. copper pads on FR-4 PCB with R<sub>θJA</sub> = 50°C/W.  
6. Pulse width ≤10μs, duty cycle ≤1%.

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1	μA	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1	—	-2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	-9 14	11 17	—	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -13A V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -10A
Forward Transconductance	g <sub>fs</sub>	—	15	—	S	V <sub>DS</sub> = -15V, I <sub>D</sub> = -8A
Diode Forward Voltage (Note 7)	V <sub>SD</sub>	-0.5	—	-1.1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -2.1A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iSS</sub>	—	2748	—	pF	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	357	—	pF	
Reverse Transfer Capacitance	C <sub>rSS</sub>	—	356	—	pF	
Gate Resistance	R <sub>G</sub>	—	2.0	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V f = 1.0MHz
<b>SWITCHING CHARACTERISTICS (Note 8)</b>						
Total Gate Charge	Q <sub>g</sub>	—	30.0 60.4	—	nC	V <sub>DS</sub> = -10V, V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -13A V <sub>DS</sub> = -10V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -13A V <sub>DS</sub> = -10V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -13A V <sub>DS</sub> = -10V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -13A
Gate-Source Charge	Q <sub>gs</sub>	—	7.2	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	16.4	—		
Turn-On Delay Time	t <sub>d(on)</sub>	—	11.2	—	ns	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -1A, R <sub>G</sub> = 6.0Ω
Rise Time	t <sub>r</sub>	—	12.4	—		
Turn-Off Delay Time	t <sub>d(off)</sub>	—	104.9	—		
Fall Time	t <sub>f</sub>	—	61.7	—		

Notes: 7. Short duration pulse test used to minimize self-heating effect.  
8. Guaranteed by design. Not subject to product testing.

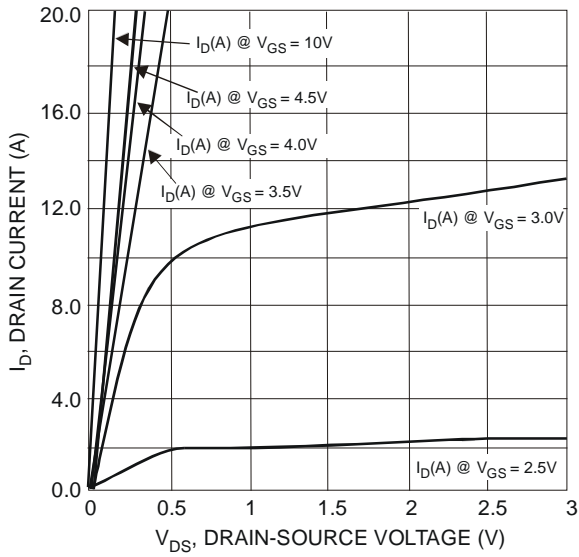


Fig. 1 Typical Output Characteristics

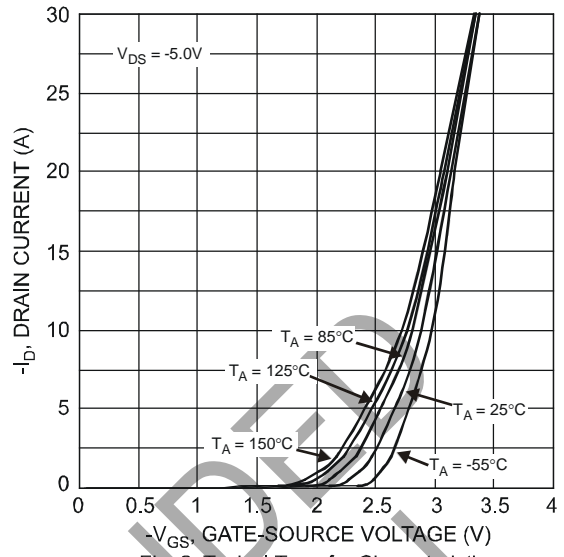


Fig. 2 Typical Transfer Characteristics

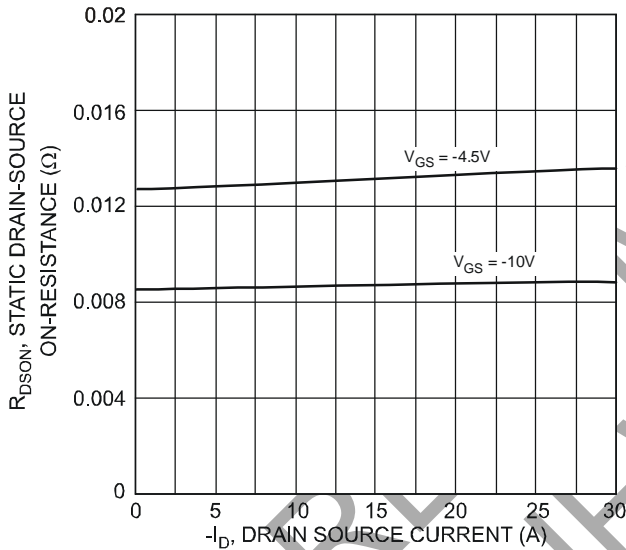


Fig. 3 On-Resistance vs. Drain Current & Gate Voltage

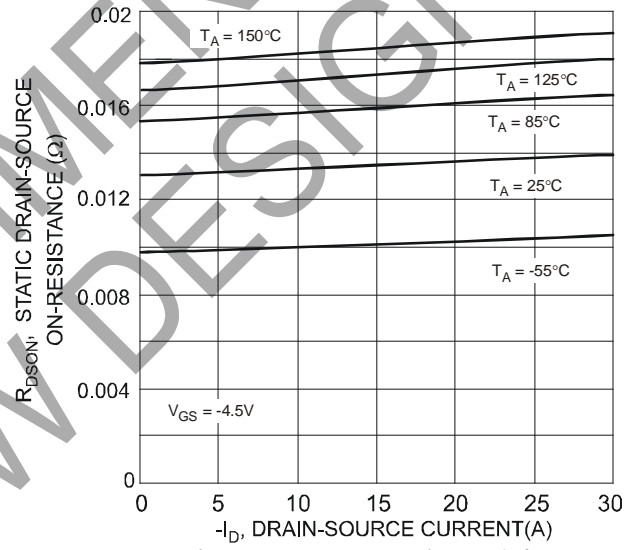


Fig. 4 On-Resistance vs. Drain Current & Gate Voltage

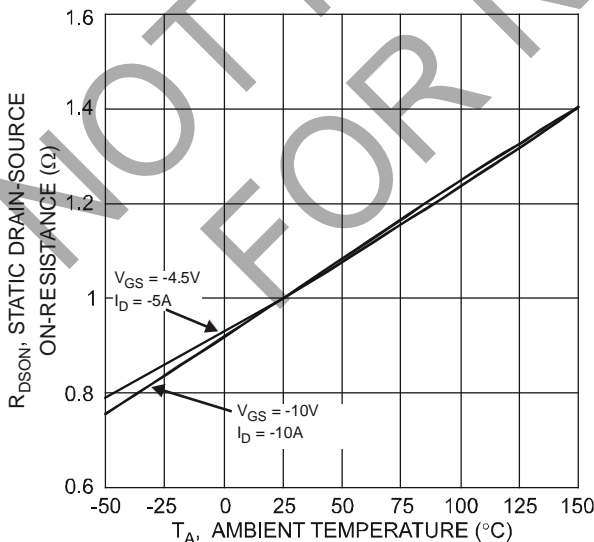


Fig. 5 Static Drain-Source On-Resistance vs. Ambient Temperature

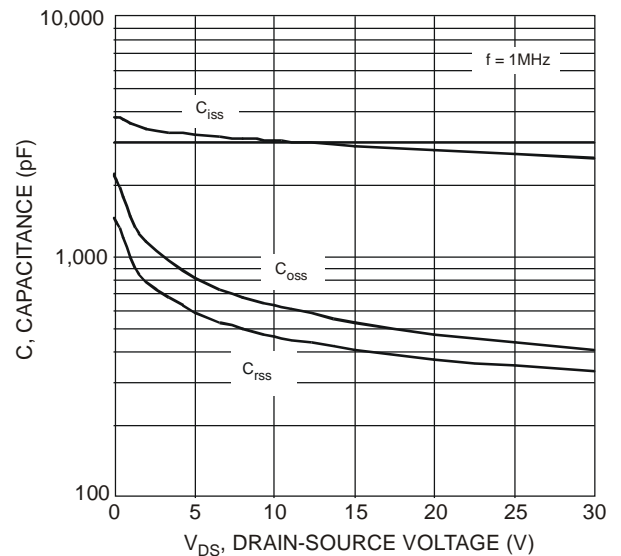


Fig. 6 Typical Total Capacitance

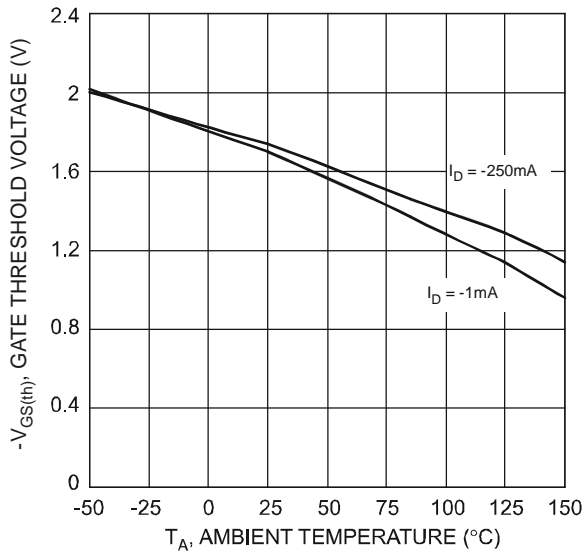


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

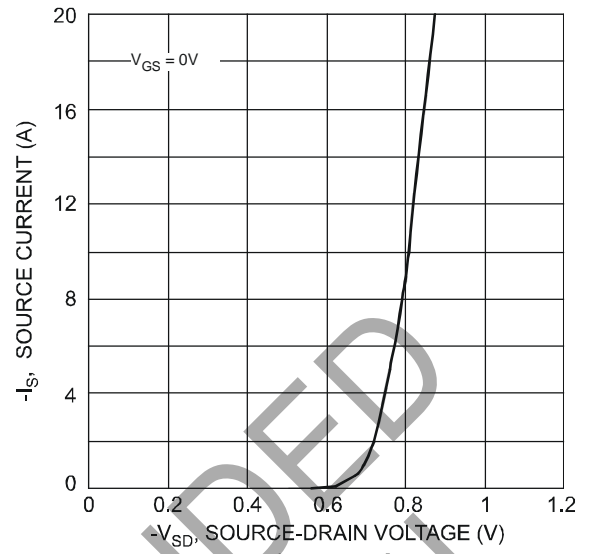


Fig. 8 Forward Drain Current vs. Source-Drain Voltage

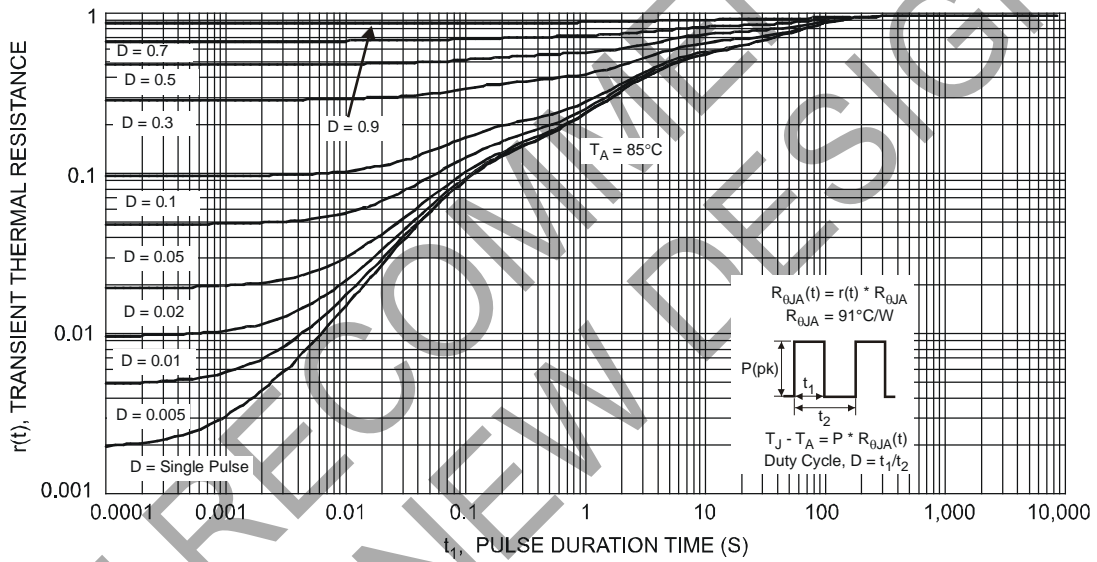
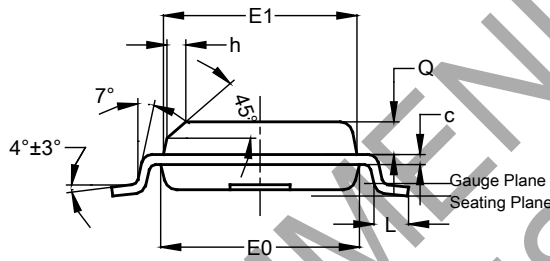
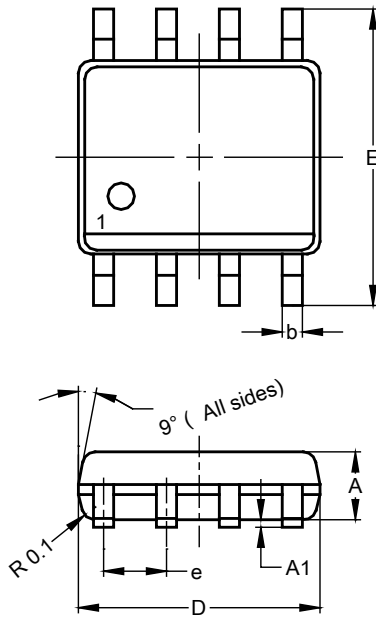


Fig. 9 Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SO-8**

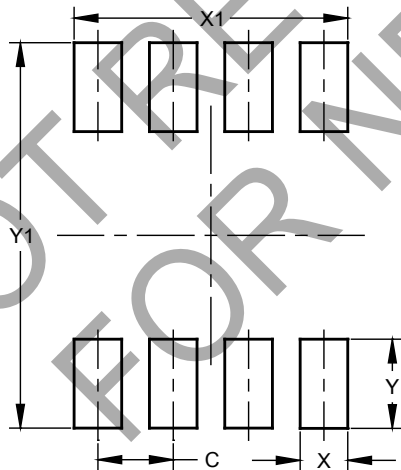


SO-8			
Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	--	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SO-8**



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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